

# KK1200-FAST SWITCHING THYRISTOR

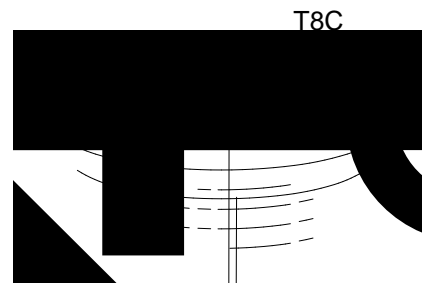
1800-2000 V<sub>DRM</sub>

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## HIGH POWER THYRISTOR FOR INVERTER APPLICATION

### Features:

- . All Diffused Structure
- . Amplifying Gate Configuration
- . Blocking capability up to 2000 volts
- . High dv/dt Capability
- . Pressure Assembled Device



## ELECTRICAL CHARACTERISTICS AND RATINGS

### Blocking - Off State

Device Type	V <sub>RRM</sub> (1)	V <sub>DRM</sub> (1)	V <sub>RSM</sub> (1)
KK1200/18	1800	1800	2000
KK1200/20	2000	2000	2100

V<sub>RRM</sub> = Repetitive peak reverse voltage

V<sub>DRM</sub> = Repetitive peak off state voltage

V<sub>RSM</sub> = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage and off state leakage	I <sub>RRM</sub> /I <sub>DRM</sub>	5 mA 80 mA (3)
Critical rate of voltage rise	dv/dt (4)	1000 V/μs

### Conducting - On State

# ELECTRICAL CHARACTERISTICS AND RATINGS K1200-FAST SWITCHING THYRISTOR

General

Parameter	Symbol	Min.	Max.	Type	Units	Conditions
Power dissipation	$P_{GM}$		20		W	
Average gate power dissipation	$P_{G(AV)}$		4		W	

Electrical

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Mechanical

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Supplier Management

Product Development

Manufacturing

Assembly

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Inspection

Packaging

Shipping

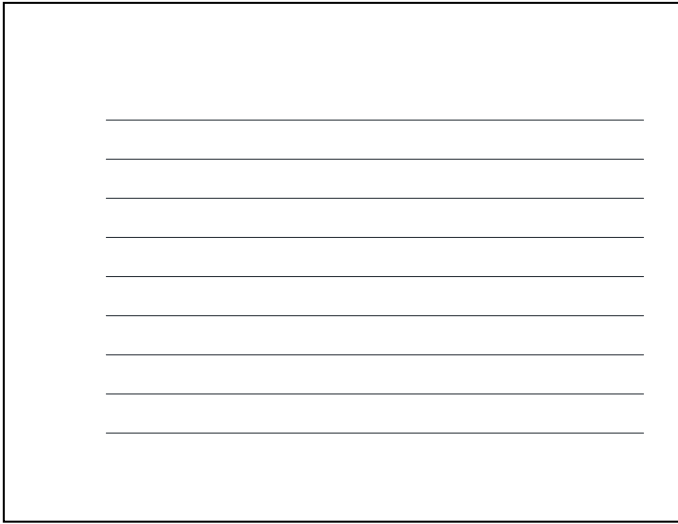
Receiving

Storage

Distribution

Customer Support

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**ELECTRICAL CHARACTERISTICS AND RATINGS KK1200-FAST SWITCHING THYRISTOR**

